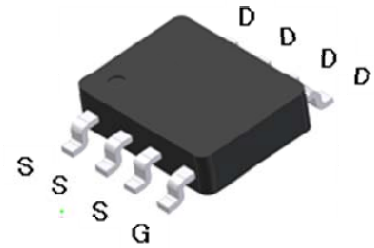


P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	-100V
$R_{DS(on)} (MAX.)$	120m Ω
I_D	-3.4A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	-3.4	A
	$T_A = 70^\circ\text{C}$		-2.7	
Pulsed Drain Current ¹		I_{DM}	-13.6	
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2.5	W
	$T_A = 70^\circ\text{C}$		1.6	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		25	$^\circ\text{C} / \text{W}$
Junction-to-Ambient ³	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³50 $^\circ\text{C} / \text{W}$ when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-2.0	-3.0	-4.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -80V, V _{GS} = 0V			-1	μA
		V _{DS} = -70V, V _{GS} = 0V, T _J = 125 °C			-10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = -5V, V _{GS} = -10V	-3.4			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = -10V, I _D = -3.4A		105	120	mΩ
Forward Transconductance ¹	g _{fs}	V _{DS} = -5V, I _D = -3.4A		8		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -25V, f = 1MHz		3520		pF
Output Capacitance	C _{oss}			132		
Reverse Transfer Capacitance	C _{rss}			115		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		5.5		Ω
Total Gate Charge ^{1,2}	Q _g	V _{DS} = -80V, V _{GS} = 10V, I _D = -3.4A		59		nC
Gate-Source Charge ^{1,2}	Q _{gs}			14		
Gate-Drain Charge ^{1,2}	Q _{gd}			11		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = -15V, I _D = -1A, V _{GS} = -10V, R _{GS} = 6Ω		15		nS
Rise Time ^{1,2}	t _r			45		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			50		
Fall Time ^{1,2}	t _f			50		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I _S				-2.3	A
Pulsed Current ³	I _{SM}				-9.2	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			-1.3	V
Reverse Recovery Time	t _{rr}	I _F = I _S , dI _F /dt = 100A / μS		150		nS
Reverse Recovery Charge	Q _{rr}			830		nC

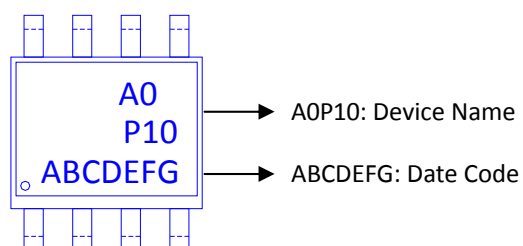
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

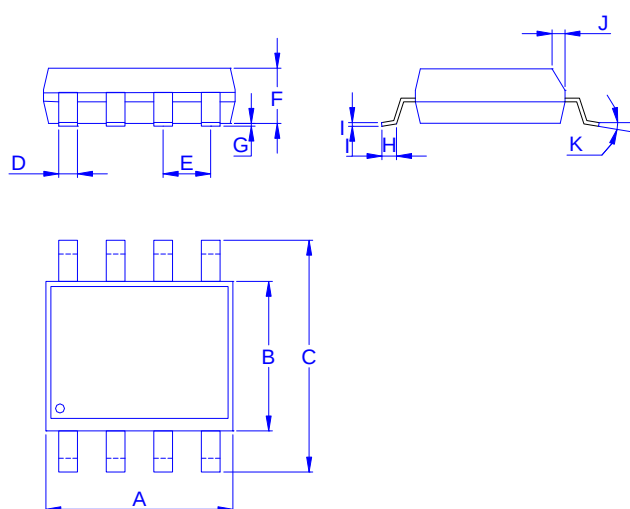
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: LBA0P10H for SOP-8



Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
Min.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°

